

Structural Changes Resulting from Doping Ti_2O_3 with Sc_2O_3 or Al_2O_3

CATHERINE E. RICE AND WILLIAM R. ROBINSON*

Department of Chemistry, Purdue University, West Lafayette, Indiana 47907

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The crystal structures of $(\text{Ti}_{1-x}\text{Sc}_x)_2\text{O}_3$, $x = 0.0038, 0.0109, \text{ and } 0.0413$, and of $(\text{Ti}_{0.99}\text{Al}_{0.01})_2\text{O}_3$, have been determined from X-ray diffraction data collected from single crystals using an automated diffractometer, and have been refined to weighted residuals of 0.025–0.034. Cell constants have also been determined for $x = 0.0005, 0.0019, \text{ and } 0.0232$. The compounds are rhombohedral, space group $R\bar{3}c$, and are isomorphous with $\alpha\text{-Al}_2\text{O}_3$. The hexagonal cell dimensions range from $a = 5.1573(2) \text{ \AA}$, $c = 13.613(1) \text{ \AA}$ for $(\text{Ti}_{0.9995}\text{Sc}_{0.0005})_2\text{O}_3$ to $a = 5.1659(4) \text{ \AA}$, $c = 13.644(1) \text{ \AA}$ for $(\text{Ti}_{0.9587}\text{Sc}_{0.0413})_2\text{O}_3$, and $a = 5.1526(2) \text{ \AA}$, $c = 13.609(1) \text{ \AA}$ for $(\text{Ti}_{0.99}\text{Al}_{0.01})_2\text{O}_3$. Sc and Al substitution cause similar increases in the short near-neighbor metal–metal distance across the shared octahedral face; for Sc doping the increase is from 2.578(1) \AA in pure Ti_2O_3 to 2.597(1) \AA in $(\text{Ti}_{0.9587}\text{Sc}_{0.0413})_2\text{O}_3$. By contrast, changes in the metal–metal distance across the shared octahedral edge appear to be governed by ionic size effects. The distance increases from 2.994(1) \AA in Ti_2O_3 to 3.000(1) \AA in $(\text{Ti}_{0.9587}\text{Sc}_{0.0413})_2\text{O}_3$ and decreases to 2.991(1) \AA in $(\text{Ti}_{0.99}\text{Al}_{0.01})_2\text{O}_3$.

Ti_2O_3 undergoes a gradual semiconductor–metal transition with a concomitant distension of the crystal lattice when it is heated through the 150–350°C temperature region (1–5). Doping Ti_2O_3 with V_2O_3 also induces a transition to metallic behavior which is electrically (6, 7) and crystallographically (6, 8, 9) similar to the transition caused by heating the pure material. In both cases the structural and electrical changes can be explained in terms of changes in metal–metal bond order which accompany the closing of a small gap between filled and empty d bands in the band structure of the semiconducting phase (7, 10).

The properties of Ti_2O_3 doped with Sc_2O_3 are less well understood. Resistivity measurements indicate that the band gap first decreases, then increases with increasing scandium substitution (11). The dependence of the lattice parameters on scandium concentration appeared (11) to be exactly opposite to that found with vanadium doping. In order to investigate the causes for this unusual

behavior, we have determined the crystal structures of $(\text{Ti}_{1-x}\text{Sc}_x)_2\text{O}_3$ for $x = 0.0038, 0.0109, \text{ and } 0.0413$, and have redetermined the lattice parameters for three other scandium concentrations. The crystal structure of $(\text{Ti}_{0.99}\text{Al}_{0.01})_2\text{O}_3$ was also determined. Sc^{3+} and Al^{3+} both lack d electrons and so should play similar electronic roles in the Ti_2O_3 lattice, though their ionic radii differ. Thus a comparison of the structural effects of scandium and aluminum doping should help clarify whether changes in interatomic distances are due to changes in bond order or to ionic size effects.

Experimental

Samples of $(\text{Ti}_{1-x}\text{Sc}_x)_2\text{O}_3$ ($x = 0.0005, 0.0019, 0.0038, 0.0109, 0.0232, \text{ and } 0.0413$) from single crystal boules were provided by Professor Honig of this department. These were the same crystals on which resistivity and lattice parameter measurements had previously been carried out (11). A boule of $(\text{Ti}_{0.99}\text{Al}_{0.01})_2\text{O}_3$ was grown by the Purdue

* Address correspondence to this author.

Crystal Growth Facility by the same methods used for the Sc-doped samples. Spheres with radii ranging from 0.0160 to 0.0198 cm were ground from fragments of the boules. Film and diffractometer measurements for the crystals showed single-phase behavior and were compatible with the known space group $R\bar{3}c$ (No. 167). No significant violations of the space-group extinctions were observed.

Unit cell parameters and intensities were measured using an Enraf-Nonius CAD-4 automated diffractometer with graphite monochromated $\text{MoK}\alpha$ radiation. The method of data collection has been described previously (9). Hexagonal cell parameters and their ESDs, shown in Table I, were calculated by least-squares refinement of the observed 2θ values for 50 to 60 reflections per crystal, $80^\circ < 2\theta < 100^\circ$, using the program LCR-2 (12) with $\lambda(\text{MoK}\alpha_1) = 0.70926 \text{ \AA}$. The intensities of all reflections in a hemisphere of reciprocal space with $6^\circ < 2\theta < 66^\circ$ were collected for all samples whose structures were determined. After applying Lorentz polarization and spherical absorption corrections (μR ranged from 0.61 to 0.75), equivalent reflections were averaged to give 126 independent reflections for each intensity data set. Reflections with $I < \sigma(I)$ were set equal to $\frac{1}{2}\sigma(I)$ and included in the refinement.

Least-squares refinements using both isotropic and anisotropic temperature factors were carried out for each set of intensity data

TABLE I

UNIT CELL PARAMETERS FOR $(\text{Ti}_{1-x}\text{Sc}_x)_2\text{O}_3$ AND $(\text{Ti}_{0.99}\text{Al}_{0.01})_2\text{O}_3$ WITH STANDARD DEVIATIONS IN PARENTHESES

Dopant concentration	a_{hex} (Å)	c_{hex} (Å)
Pure Ti_2O_3^a	5.1580(4)	13.611(1)
0.05 at % of Sc	5.1573(2)	13.613(1)
0.19 at % of Sc	5.1586(3)	13.611(1)
0.38 at % of Sc	5.1589(2)	13.616(1)
1.09 at % of Sc	5.1598(1)	13.625(1)
2.32 at % of Sc	5.1618(2)	13.632(2)
4.13 at % of Sc	5.1659(4)	13.644(1)
1 at % of Al	5.1526(2)	13.609(1)

^a Ref. (5).

using the RFINE2 program of Finger (13). The initial atomic parameters in the space group $R\bar{3}c$ were those of Robinson (14) for Ti_2O_3 , transformed from rhombohedral to hexagonal coordinates. The program minimized $\sum w(F_o - F_c)^2$ using the scattering factors for Ti^{3+} , Sc^{3+} , Al^{3+} , and 0° (15) corrected for real and imaginary anomalous dispersion (16), weights based on average standard deviations determined from counting statistics ($w = 1/\sigma^2(F) = 4F_o^2/\sigma^2(F_o^2)$), and an extinction correction of the form $F_{\text{corr}}^2 = F_o^2(1 + sI_o^2)$. No reflections were rejected from the refinements. Final weighted R values varied from 0.025 to 0.034. Values of the standard deviation of an observation of unit weight are listed in Table II as S . The final atom parameters in Table II were used with the variance-covariance matrices to calculate the interatomic distances and angles and their ESDs listed in Table III. Structure factor amplitudes are reported in Table IV.

Results and Discussion

All crystals studied were found to be isomorphous with $\alpha\text{-Al}_2\text{O}_3$. The structures consist of approximate hexagonally closest-packed oxide layers with metal ions occupying two-thirds of the octahedral interstices (Fig. 1). A given metal ion, $M(1)$, has one near metal neighbor along the c axis with which it shares a triangular face of its coordination octahedron ($M(2)$ in Fig. 1), and three near metal neighbors in the a - b plane which share edges of the octahedron ($M(3)$ in Fig. 1).

The effects of scandium and aluminum doping on the Ti_2O_3 lattice parameters are shown in Table I. Cell constants for Ti_2O_3 (5) are also included for comparison. Many unit cell determinations (17) and three refined crystal structures from single crystal data (5, 14, 18) are available for Ti_2O_3 . This set was chosen since it was determined on the same instrument under the same conditions as the other data reported and thus comparisons of the small changes observed should not be effected by possible systematic errors between equipment or by differences in conditions.

Doping with Sc^{3+} or Al^{3+} causes only

TABLE II
CRYSTALLOGRAPHIC DATA FOR (Ti_{1-x}Sc_x)₂O₃ AND (Ti_{0.99}Al_{0.01})₂O₃ WITH STANDARD DEVIATIONS
IN PARENTHESES

Parameter	0.38 at % of Sc	1.09 at % of Sc	4.13 at % of Sc	1 at % of Al
<i>M z</i>	0.34470(5)	0.34486(5)	0.34517(4)	0.34487(4)
β_{11}^a	30(4)	28(4)	34(3)	32(4)
β_{33}^a	3.6(6)	1.7(6)	5.5(4)	4.2(4)
<i>Ox x</i>	0.3130(4)	0.3130(4)	0.3123(3)	0.3130(3)
β_{11}^a	33(8)	28(7)	35(6)	36(6)
β_{22}^a	44(11)	36(10)	52(8)	41(8)
β_{33}^a	3.3(12)	1.5(10)	5.3(8)	3.1(8)
β_{13}^a	0.8(12)	1.0(11)	1.7(10)	2.2(10)
<i>R</i>	0.024	0.026	0.018	0.019
<i>R</i> _{wt}	0.034	0.032	0.025	0.026
<i>s</i> ^b	5.2(5)	6.0(5)	3.7(3)	3.9(3)
<i>B</i> _M	0.25(3)	0.19(3)	0.32(2)	0.29(2)
<i>B</i> _{Ox}	0.28(4)	0.20(4)	0.35(3)	0.34(3)
<i>S</i>	1.00	1.00	1.00	1.07

^a Times 10⁴. For *M*, $\beta_{11} = \beta_{22}$, $\beta_{12} = \frac{1}{2}\beta_{11}$, and $\beta_{23} = \beta_{13} = 0$. For *Ox*, $\beta_{12} = \frac{1}{2}\beta_{22}$ and $\beta_{23} = 2\beta_{13}$.
The form of the anisotropic temperature factor *T* is $T = \exp(-\sum_i \sum_j h_i h_j \beta_{ij})$.

^b Times 10⁵.

TABLE III
INTERATOMIC DISTANCES (Å) AND BOND ANGLES (DEGREES) FOR (Ti_{1-x}Sc_x)₂O₃ AND (Ti_{0.99}Al_{0.01})₂O₃, WITH
STANDARD DEVIATIONS IN PARENTHESES

	Pure Ti ₂ O ₃ ^a	0.38 at % of Sc	1.09 at % of Sc	4.13 at % of Sc	1 at % of Al
Distances					
<i>M</i> (1)– <i>M</i> (2)	2.578(2)	2.579(1)	2.585(1)	2.597(1)	2.582(1)
<i>M</i> (1)– <i>M</i> (3)	2.994(1)	2.995(1)	2.996(1)	3.000(1)	2.991(1)
<i>M</i> (1)–O(1)	2.066(2)	2.066(2)	2.068(2)	2.071(1)	2.066(1)
<i>M</i> (1)–O(5)	2.027(1)	2.027(1)	2.026(1)	2.029(1)	2.024(1)
O(1)–O(2)	2.796(4)	2.797(4)	2.797(3)	2.794(3)	2.789(1)
O(1)–O(4)	2.791(1)	2.791(1)	2.792(1)	2.794(1)	2.793(2)
O(1)–O(5)	2.880(1)	2.881(1)	2.882(1)	2.887(1)	2.878(1)
O(4)–O(5)	3.073(2)	3.074(2)	3.074(2)	3.081(2)	3.070(1)
Angles					
O(1)– <i>M</i> (1)–O(2)	85.20(7)	85.17(6)	85.09(6)	84.85(4)	85.07(4)
O(1)– <i>M</i> (1)–O(4)	85.96(2)	85.97(2)	85.98(2)	85.94(1)	85.99(1)
O(1)– <i>M</i> (1)–O(5)	89.42(5)	89.45(5)	89.46(4)	89.53(4)	89.47(3)
O(1)– <i>M</i> (1)–O(6)	170.01(8)	169.99(7)	169.90(7)	169.60(5)	169.88(5)
O(4)– <i>M</i> (1)–O(5)	98.60(3)	98.60(3)	98.65(3)	98.81(2)	98.65(2)
<i>M</i> (1)–O(1)– <i>M</i> (2)	77.18(9)	77.23(8)	77.34(7)	77.66(6)	77.37(5)
<i>M</i> (1)–O(2)– <i>M</i> (3)	94.04(2)	94.03(2)	94.02(2)	94.06(1)	94.01(1)
<i>M</i> (2)–O(2)–O(3)	132.33(5)	132.34(4)	132.33(4)	132.37(3)	132.34(3)

^a Ref. (5).

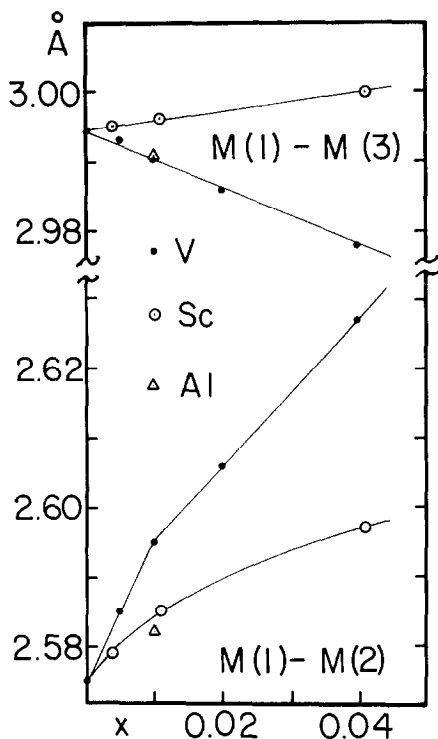


FIG. 2. Variation of metal-metal distances in $(\text{Ti}_{1-x}\text{M}_x)_2\text{O}_3$.

1% of Al substitution is almost identical to the change produced by 1% of Sc. The increase in both cases is about half that caused by the same concentration of vanadium. The metal-metal distance across the shared edge, $M(1)-M(3)$, increases from 2.994(1) Å in Ti_2O_3 to 3.000(1) Å in $(\text{Ti}_{0.9587}\text{Sc}_{0.0413})_2\text{O}_3$ while it decreases to 2.991(1) Å in $(\text{Ti}_{0.99}\text{Al}_{0.01})_2\text{O}_3$. The changes in the $M(1)-M(3)$ distance with Al and Sc doping are close to those expected due to changes in effective ionic radius, though the changes caused by V-doping are greater than one would predict on this basis alone.

Changes in metal-oxygen and oxygen-oxygen distances with Sc or Al doping are small, with a maximum change of 0.005 Å in the metal-oxygen distances. The entire structural change in both cases can be explained satisfactorily as the result of changes in the metal-metal distances coupled with reorganization of the structure in order to maintain approximately constant metal-oxygen distances.

The effects of doping Ti_2O_3 with Sc or Al can be understood in terms of the band-crossing scheme proposed (10) to account for the electrical behavior of pure Ti_2O_3 . In this model the valence band, a band of a_1 symmetry, is formed by the bonding interaction between d_{z^2} orbitals of c axis neighbor metal ions, $M(1)$ and $M(2)$. This band is completely filled at 0°K. At low temperatures, the valence band is separated by a small gap from the conduction band, of e symmetry, which is formed by overlap of d orbitals of near-metal neighbors in the $a-b$ plane ($M(1)$ and $M(3)$). The semiconductor-metal transitions caused in Ti_2O_3 by heating or by doping with vanadium involve removal of electrons from the a_1 band with a decrease in the $M(1)-M(2)$ bond order and a concomitant increase in the $M(1)-M(2)$ distance. This increase of the $M(1)-M(2)$ distance destabilizes the a_1 band so that it rises in energy and eventually overlaps the e band, resulting in metallic behavior. Single-crystal X-ray studies have confirmed that substantial increases in the $M(1)-M(2)$ distance accompany the electrical transitions in both pure and V-doped Ti_2O_3 (4, 5, 9). The detailed mechanisms for these transitions using this model have been discussed elsewhere (2, 7, 10).

Since neither Sc^{3+} nor Al^{3+} possesses d electrons, these ions are not likely to participate in metal-metal bonding in the Ti_2O_3 host lattice. Thus the addition of each Sc^{3+} or Al^{3+} ion should disrupt one $M(1)-M(2)$ bond, increasing the average $M(1)-M(2)$ distance and generally dilating the structure in the c direction. As the $M(1)-M(2)$ distance increases, the a_1 band should then rise in energy and cause the band gap to decrease (10, 21, 22). This would explain why the activation energy for conduction, ϵ_a , initially decreases as Sc is added to Ti_2O_3 . The eventual increase in ϵ_a with greater Sc substitution can be related to the increase in the $M(1)-M(3)$ distance, which increases more slowly with increasing dopant concentration than does the $M(1)-M(2)$ distance. The e band in Ti_2O_3 formed by overlap between orbitals of $M(1)$ and $M(3)$ has been shown to be narrow (21, 22), probably because the $M(1)-M(3)$ distance is already rather long for effective

metal-metal overlap. The increase in this distance caused by the greater size of the Sc^{3+} ion and the presence of the dopant ion should narrow the e band even more. This, though the $M(1)$ - $M(2)$ increase should cause the a_1 and e band centers to move together, band narrowing may widen the band gap when the dopant concentration is sufficiently large.

The structural effects of Sc substitution in Ti_2O_3 are thus compatible with the Ti_2O_3 band structure and with the observed non-monotonic dependence of ϵ_a on dopant concentration (11). The structure of $(\text{Ti}_{0.99}\text{Al}_{0.01})_2\text{O}_3$ tends to confirm our interpretation. Since Sc and Al substitution have similar effects on the $M(1)$ - $M(2)$ distance, this change must be due to a change in bond order. The changes in the $M(1)$ - $M(3)$ distance with doping, however, are apparently related to ionic size effects. Resistivity measurements on a series of aluminum doped Ti_2O_3 samples are in progress to check the variation of ϵ_a with the $M(1)$ - $M(3)$ distance.

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